

CLAIMS

1. A structure situated in a semiconductor die, said structure comprising:
an active shield situated in a substrate, said active shield comprising a salicide
layer situated on an active region, said active shield having a first conductivity type;

5 a passive component situated in an interconnect metal layer in said semiconductor
die, said passive component being situated above said active shield;

wherein said active shield defines an AC ground for said passive component.

2. The structure of claim 1 further comprising at least one contact, said at
10 least one contact connecting said active shield to a semiconductor die AC ground.

3. The structure of claim 1 further comprising a well situated in said substrate,
said active shield being situated in said well, said well having a second conductivity type.

15 4. The structure of claim 1 wherein said active shield comprises a plurality of
fingers, each of said plurality of fingers comprising a salicide segment situated on an
active segment.

5. The structure of claim 1 wherein said passive component is an inductor.

20 6. The structure of claim 3 further comprising a salicided active region
situated in said well, said salicided active region being situated adjacent to at least one

side of said active shield, said salicided active region having said second conductivity type.

7. The structure of claim 1 wherein said salicide layer is selected from the
5 group consisting of titanium silicide, cobalt silicide, and nickel mono-silicide.

8. The structure of claim 3 wherein said well is connected to a voltage source,
said voltage source being greater than or equal to ground voltage, said voltage source
having no AC component.

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9. The structure of claim 1 further comprising a well situated in said substrate,
said active shield being situated in said well, said well having said first conductivity type.

10. A structure situated in a semiconductor die, said structure comprising:
15 a well situated in a substrate, said well having a first conductivity type;
an active shield situated in said well, said active shield comprising a salicide layer
situated on an active region in said well, said active shield having a second conductivity
type;

a passive component situated in an interconnect metal layer in said semiconductor
20 die, said passive component being situated above said active shield;
wherein said active shield defines an AC ground for said passive component.

11. The structure of claim 10 further comprising at least one contact, said at least one contact connecting said active shield to a semiconductor die AC ground.

12. The structure of claim 10 wherein said active shield comprises a plurality of
5 fingers, each of said plurality of fingers comprising a salicide segment situated on an active segment.

13. The structure of claim 10 further comprising a salicided active region situated adjacent to at least one side of said active shield, said salicided active region
10 having a first conductivity type.

14. The structure of claim 10 wherein said passive component is an inductor.

15. The structure of claim 13 wherein said salicided active region is connected
15 to a voltage source, said voltage source being greater than or equal to ground voltage, said voltage source having no AC component.

16. The structure of claim 10 wherein said salicide layer is selected from the group consisting of titanium silicide, cobalt silicide, and nickel mono-silicide.

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17. A structure situated in a semiconductor die, said structure comprising:
a well situated in a substrate, said well having a first conductivity type;

an active shield situated in said well, said active shield comprising a plurality of fingers, each of said plurality of fingers comprising a salicide segment situated on an active segment, said plurality of fingers having a second conductivity type;

a passive component situated in an interconnect metal layer in said semiconductor die, said passive component being situated above said active shield;

wherein said active shield defines an AC ground for said passive component.

18. The structure of claim 17 further comprising at least one contact, said at least one contact connecting said active shield to a semiconductor die AC ground.

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19. The structure of claim 17 further comprising a salicided active region situated adjacent to at least one side of said active shield, said salicided active region having said first conductivity type.

15 20. The structure of claim 17 wherein said passive component is an inductor, wherein said plurality of fingers terminate an electric field of said inductor.

21. The structure of claim 19 wherein said salicided active region is connected to a voltage source, said voltage source being greater than or equal to ground voltage, said voltage source having no AC component.

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